EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	28	cutting-off adj plate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/02 14:54
S48	927	349/149	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:31
S49	963	349/187	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:26
S50	27	cutting-off adj plate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/02 14:54
S51	4883	expos$4 near10 pad near10 etch$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 15:38
S52	237	(expos$4 near10 pad near10 etch$4) and gate and data and semiconductor and pixel and mask$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 11:15

S53	239	("1954691" | "2851408" | "2867541" | "2959483" | "3070441" | "3108904" | "3259782" | "3314871" | "3360450" | "3525679" | "3554889" | "3665241" | "3675063" | "3755704" | "3789471" | "3808048" | "3812559" | "3855499" | "3898146" | "3947716" | "3970887" | "3998678" | "4008412" | "4075535" | "4084942" | "4139773" | "4141405" | "4143292" | "4164680" | "4168213" | "4178531" | "4307507" | "4350926" | "4482447" | "4498952" | "4507562" | "4512912" | "4513308" | "4540983" | "4542038" | "4578614" | "4588921" | "4594527" | "4633131" | "4647400" | "4663559" | "4684353" | "4684540" | "4685996" | "4687825" | "4687938" | "4710765" | "4721885" | "4728851" | "4758449" | "4763187" | "4780684" | "4788472" | "4816717" | "4818914" | "4822466" | "4827177" | "4835438" | "4851254" | "4855636" | "4857161" | "4857799" | "4874981" | "4882659" | "4889690" | "4892757" | "4899081" | "4900584" | "4908539" | "4923421" | "4926056" | "4933108" | "4940916" | "4943343" | "4956202" | "4956574" | "4964946" | "4987007" | "4990416" | "4990766" | "4994205" | "5007873" | "5015912" | "5019003" | "5036247" | "5038070" | "5043715" | "5054046" | "5054047" | "5055077" | "5055744" | "5057047" | "5063323" | "5063327" | "5064396" | "5066883" | "5075591" | "5075595" | "5075596" | "5079476" | "5085958" | "5089292" | "5089742" | "5089812" | "5090932" | "5098737" | "5101137" | "5101288" | "5103144" | "5103145" | "5117267" | "5117299" | "5119386" | "5123039" | "5124072" | "5124558" | "5126287" | "5129850" | "5132585" | "5132676").PN. OR ("5136764"	"5138237"	"5140219"	"5141459"	"5141460"	"5142184"	"5142256"	"5142390"	"5144191"	"5148078"	"5148461"	"5150011"	"5150192"	"5151061"	"5153753"	"5153901"	"5155420"	"5156770"	"5157304"	"5157309"	"5162704"	"5166456"	"5173634"	"5173635"	"5173697"	"5180951"	"5183529"	"5185178"	"5186670"	"5187578"	"5191217"	"5192240"	"5194780"	"5199917"	"5199918"	"5201992"	"5202571"	"5203731"	"5204021"	"5204581"	"5205770"	"5209687"	"5210430"	"5210462"	"5212426"	"5213712"	"5214346"	"5214347"	"5214416"	"5220725"	"5227699"		US-PGPUB; USPAT; USOCR	OR	OFF	2005/05/19 16:28

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S54	24	(expos$4 near10 pad near10 (dry adj etch$4)) and gate and data and semiconductor and pixel and mask$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 16:29
S55	94	(expos$4 near10 pad near10 etch$4) and gate and data and semiconductor and pixel and mask$4 and cut$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 11:08
S56	2	(expos$4 near10 pad near10 etch$4) and gate and data and semiconductor and pixel and mask$4 and cut$4-off	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 11:08
S57	998	349/143	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:24
S58	367	349/150	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:24
S59	1653	349/43	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:25
S60	357	349/43 and pad and expos$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:32
S61	73	349/150 and pad and expos$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33

S62	131	349/152 and pad and expos$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:32
S63	114	349/143 and pad and expos$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/13 11:21
S65	84	349/143 and pad and expos$4 and mask$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S67	66	349/152 and pad and expos$4 and mask$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S69	291	349/43 and pad and expos$4 and mask$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/21 10:39
S70	111	(expos$4 near10 pad near10 etch$4) and gate and data and semiconductor and pixel and mask$4 and ((mask cutting-off) near10 metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:08
S71	9	(expos$4 near10 pad near10 etch$4) and gate and data and semiconductor and pixel and mask$4 and ((mask cutting-off) near10 metal) and ((three "3") adj mask$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 12:54
S72	1857216	(dry adj etch$4) nea10 insulat$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:11

S73	4990943	S72 (liquid adh crystal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:10
S74	2348219	S72 (liquid adh crystal) and expos$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:10
S75	150088	(dry adj etch$4) nea10 insulat$4 near10 expos$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:15
S76	11537	S75 and (liquid adj crystal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:12
S77	2992	(S75 near10 remov$4)and (liquid adj crystal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:13
S78	833	(S75 near10 remov$4)and (liquid adj crystal) and pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:13
S79	228	(S75 near10 remov$4)and (liquid adj crystal) and (gate adj pad) and (data adj pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:14
S80	1281	(dry adj etch$4) near10 insulat$4 near10 expos$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:15

S81	40	(dry adj etch$4) near10 insulat$4 near10 expos$4 and (gate adj pad) and (data adj pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/23 17:16
S82	401	349/43 and pad and expos$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:32
S83	155	349/152 and pad and expos$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:32
S84	96	349/143 and pad and expos$4 and mask$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S85	86	349/150 and pad and expos$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S86	80	349/152 and pad and expos$4 and mask$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/15 13:33
S88	146	349/143 and pad and expos$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/13 11:21
S89	425	349/43 and pad and expos$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/13 11:21

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S90	1193	349/187	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/13 11:21
S91	1096	349/187 and @ad<"20031117"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:26
S92	493	349/187 and @ad<"20031117" and mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:34
S93	508	349/187 and @ad<"20031117" and mask$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:36
S94	605	"349"/$.ccls. and @ad<"20031117" and mask$4 and gate and data and pad and pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/27 15:41
S95	104	"349"/$.ccls. and @ad<"20031117" and mask$4 and gate and data and pad and pixel and (thin adj film adj transistor adj array)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 16:16
S96	565	"349"/$.ccls. and @ad<"20031117" and mask$4 and gate and data and pad and pixel and ((thin adj film adj transistor adj array) TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:21
S97	67	"349"/$.ccls. and @ad<"20031117" and mask$4 and gate and data and pad and pixel and ((thin adj film adj transistor adj array) TFT) and (cut$4 near10 off)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 16:55

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S98	22	"349"/$.ccls. and @ad<"20031117" and mask$4 and gate and data and pad and pixel and ((thin adj film adj transistor adj array) TFT) and (cut$4 near10 off) and protect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 16:56
S99	129454	((protect$4 passivation) near10 substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:22
S10 0	8486	S99 and (liquid adj crystal) and (mask cutt$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:25
S10 1	3687	S100 and gate and data	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:24
S10 2	3387	S100 and gate and data and pixel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:25
S10 3	13	S99 and (liquid adj crystal) and mask and cutt$4-off	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:26
S10 4	7424	S99 and (liquid adj crystal) and mask	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:26

S10 5	2114	S99 and (liquid adj crystal) and mask and pad	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:26
S10 6	1031	S99 and (liquid adj crystal) and mask and pad and cut$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:26
S10 7	930	S99 and (liquid adj crystal) and mask and pad and cut$4 and etch$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:27
S10 8	405	S99 and (liquid adj crystal) and (mask with process) and pad and cut$4 and etch$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:29
S10 9	19	S99 and (liquid adj crystal) and (mask with process) and pad and (cut$4 with plate) and etch$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:28
S11 0	261	S99 and (liquid adj crystal) and (mask with process) and pad and cut$4 and etch$4 and @ad<"20031117"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/09 17:29